

isc Silicon NPN Power Transistor

2SC3479

DESCRIPTION

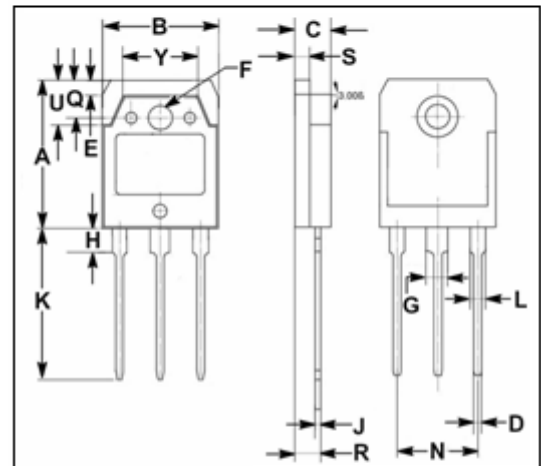
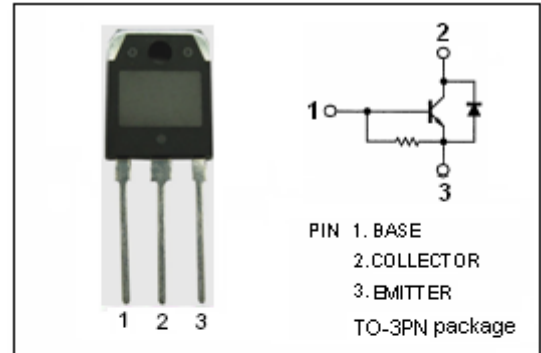
- High Breakdown Voltage-
: $V_{CBO}= 1500V$ (Min)
- High Switching Speed
- High Reliability
- Built-in Damper Diode

APPLICATIONS

- Designed for high definition CRT display horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current- Continuous	2.5	A
I_{CP}	Collector Current-Pulse	8	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	80	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



DIM	mm	
	MIN	MAX
A	19.90	20.10
B	15.38	15.42
C	4.75	4.85
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.98	3.02
H	3.20	3.40
J	0.595	0.605
K	19.95	20.25
L	1.98	2.02
N	10.89	10.91
Q	4.95	5.05
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}; R_{BE}=\infty$	800			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C=5\text{mA}; I_E=0$	1500			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=200\text{mA}; I_C=0$	7			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.8\text{A}$			8.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2.5\text{A}; I_B=0.8\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=800\text{V}; I_E=0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=4\text{V}; I_C=0$	40		130	mA
h_{FE}	DC Current Gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	8			
V_{ECF}	C-E Diode Forward Voltage	$I_F=2.5\text{A}$			2.0	V
f_T	Current-Gain—Bandwidth Product	$I_C=0.5\text{A}; V_{CE}=10\text{V}$		3		MHz
t_f	Fall Time	$I_C=2\text{A}, I_{B1}=0.4\text{A}; I_{B2}=-0.8\text{A}$			0.3	μs